

PATENT ABSTRACTS OF JAPAN

(11)Publication number : **2000-340567**

(43)Date of publication of application : **08.12.2000**

(51)Int.CI.

H01L 21/3205

G02F 1/1333

G02F 1/1365

H01L 21/304

H01L 29/786

H01L 21/336

H05K 3/46

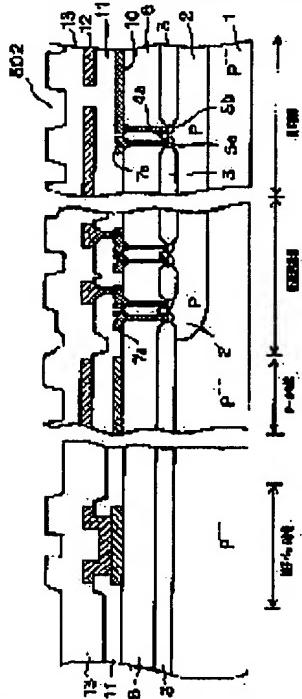
(21)Application number : **11-152266**

(71)Applicant : **SEIKO EPSON CORP**

(22)Date of filing : **31.05.1999**

(72)Inventor : **HIRABAYASHI YUKIYA
KAWADA HIDENORI**

(54) SUBSTRATE FLATTENING METHOD, MANUFACTURE OF ELECTRO-OPTICAL DEVICE, AND MANUFACTURE OF SEMICONDUCTOR DEVICE



(57)Abstract:

PROBLEM TO BE SOLVED: To provide a method for flattening a substrate, which can reduce the time necessary for a polishing step and can reduce the amount of slurry (abrasive liquid) used by obtaining a uniform polishing rate in the surface of a substrate.

SOLUTION: Prior to the step of polishing an insulating film 13 of a liquid crystal device, recesses 502 are etched in the surface of the insulating film, corresponding to a pixel or seal region having a low polishing rate. Thereby slurry can enter into the recesses 502, an apparent polishing rate can be increased, and a uniform polishing rate in the surface of a substrate in the polishing step can be obtained.

LEGAL STATUS

[Date of request for examination] 02.07.2003

[Date of sending the examiner's decision of rejection]

[Kind of final disposal of application other than the examiner's decision of rejection or application converted registration]

[Date of final disposal for application]

[Patent number]

[Date of registration]

[Number of appeal against examiner's decision of rejection]

[Date of requesting appeal against examiner's decision of rejection]

[Date of extinction of right]

Copyright (C); 1998,2003 Japan Patent Office